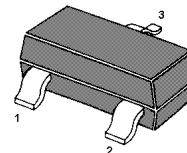
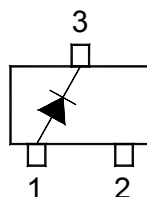


MMBD193

SILICON EPITAXIAL PLANAR DIODE Ultra High Speed Switching Application



1. ANODE 3. CATHODE

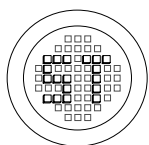
Marking Code: **F3**
SOT-23 Plastic Package

Absolute Maximum Ratings ($T_a=25^{\circ}\text{C}$)

	Symbol	Value	Unit
Peak Reverse Voltage	V_{RM}	85	V
Reverse Voltage	V_R	80	V
Peak Forward Current	I_{FM}	300	mA
Average Forward Current	I_O	100	mA
Surge Current (10ms)	I_{FSM}	2	A
Power Dissipation	P_{tot}	150	mW
Junction Temperature	T_J	150	$^{\circ}\text{C}$
Storage Temperature Range	T_s	-55 to 150	$^{\circ}\text{C}$

Characteristics at $T_a = 25^{\circ}\text{C}$

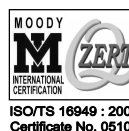
	Symbol	Min.	Typ.	Max.	Unit
Forward Voltage $I_F = 1\text{mA}$	V_F	-	0.6	-	V
$I_F = 10\text{mA}$	V_F	-	0.72	-	V
$I_F = 100\text{mA}$	V_F	-	0.9	1.2	V
Reverse Current $V_R = 80\text{V}$	I_R	-	-	0.5	μA
Total Capacitance $V_R = 0\text{V}$, $f = 1\text{MHz}$	C_{tot}	-	0.9	3	pF
Reverse Recovery Time $I_F = 10\text{mA}$	t_{rr}	-	1.6	4	ns



®

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